

SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF
ABSTRACT

A metal bump made of a first kind of metal is formed on an electrode pad of a semiconductor chip, and a lead frame having a fine wire lead of a three-layered structure comprising a lower layer constituted with a second kind of metal, an intermediate layer and an upper layer is bonded at the lower layer thereof with the metal bump to provide a semiconductor device in which thermal and mechanical impact shocks are moderated during bonding in an electrode pad on a semiconductor chip and a fine wire lead frame of a multilayered structure to attain bonding at high reliability and a manufacturing method thereof.

Figure 19